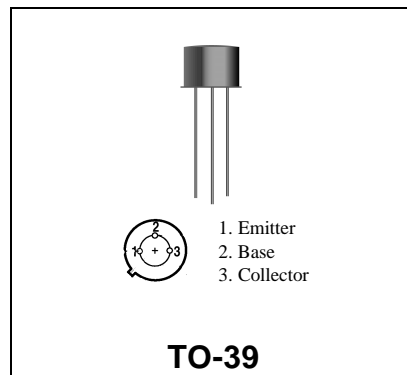


**2N6255**

**RF & MICROWAVE DISCRETE  
 LOW POWER TRANSISTORS**

Features

- Silicon NPN, To-39 packaged VHF Transistor
- 3.0 Watt Power Output @ 175 MHz
- Power Gain,  $G_{PE} = 7.8$  dB
- Efficiency = 50%



DESCRIPTION:

Silicon NPN transistor, designed for 12.5 volt VHF equipment. Applications include amplifier; pre-driver, driver, and output stages. Also suitable for oscillator and frequency-multiplier functions.

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$ )

Symbol	Parameter	Value	Unit
$V_{CEO}$	Collector-Emitter	18	Vdc
$V_{CBO}$	Collector-Base Voltage	36	Vdc
$V_{EBO}$	Emitter-Base Voltage	4.0	Vdc
$I_C$	Collector Current	1	A

Thermal Data

$P_D$	Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	5.0 28.5	Watts mW/ $^{\circ}C$
-------	--	-------------	--------------------------

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC  
 (off)

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BVCES	Collector-Emitter Breakdown Voltage (IC = 5.0 mA <sub>dc</sub> , VBE = 0V <sub>dc</sub> )	36	-	-	V <sub>dc</sub>
BVCEO	Collector-Emitter Breakdown Voltage (IC=10 mA <sub>dc</sub> , IB=0)	18	-	-	V <sub>dc</sub>
BVEBO	Emitter-Base Breakdown Voltage (IE = 1.0 mA <sub>dc</sub> , IC = 0)	4.0	-		V <sub>dc</sub>
ICES	Collector Cutoff Current (VCE = 15 V <sub>dc</sub> , VBE = 0 V <sub>dc</sub> )	-	-	5.0	mA
ICBO	Emitter Cutoff Current (VCB = 15 V <sub>dc</sub> , IE = 0)	-	-	.25	mA

(on)

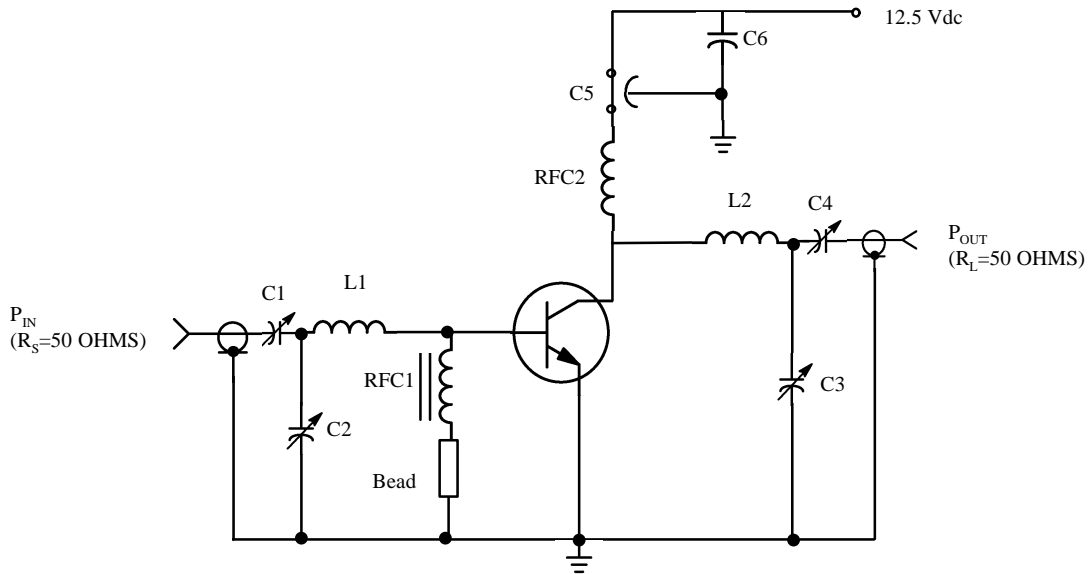
HFE	DC Current Gain (IC = 250 mA <sub>dc</sub> , VCE = 5.0 V <sub>dc</sub> )	5.0	-	-	-
-----	---	-----	---	---	---

DYNAMIC

Symbol	Test Conditions	Value			Unit
COB	Output Capacitance (VCB = 12.5V <sub>dc</sub> , f = 1.0 MHz)	-	15	20	pF

FUNCTIONAL

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
G <sub>PE</sub>	Power Gain	Test Circuit-Figure 1 P <sub>out</sub> = 3.0 W, VCC = 12.5V <sub>dc</sub> f = 175 MHz	7.8	-	-	dB
η <sub>c</sub>	Collector Efficiency	Test Circuit-Figure 1 P <sub>out</sub> = 3.0 W, VCC = 12.5V <sub>dc</sub> f = 175 MHz	50	-	-	%



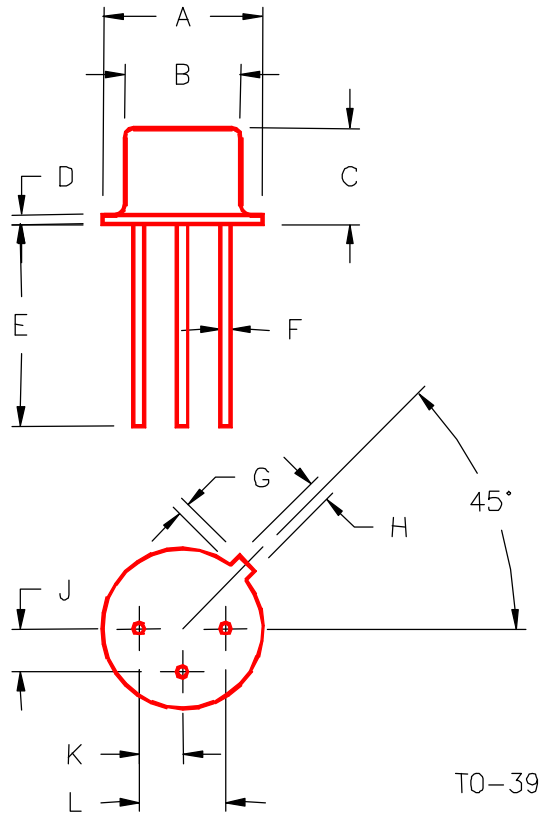
**Figure 1 - 175 MHz RF AMPLIFIER CIRCUIT FOR  $G_{PE}$ ,  
 AND EFFICIENCY SPECIFICATIONS.**

C1,3: 2.0-50 pF ARCO 461 ELEMENCO  
 C5: 1000 pF FEED THRU  
 L1: 1 TURN #18 AWG ¼" I.D.  
 RFC2: 0.15 uH MOLDED CHOKE

C2,4: 5.0-80 pF ARCO 462 ELEMENCO  
 C6: 5.0 uF  
 L2: 2 1/2 TURNS #18 AWG ¼" I.D.  
 BEAD: FERROXCUBE 56-570-65/3B

RFC1: 0.15 uH MOLDED CHOKE WITH BEAD ON GROUND LEG

PACKAGE STYLE M246



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.350/8,89	.370/9,40	J	.095/2,41	.105/2,67
B	.315/8,00	.335/8,51	K	.095/2,41	.105/2,67
C	.240/6,10	.260/6,60	L	.190/4,83	.210/5,33
D	.015/0,38	.045/1,14			
E	.500/12,70				
F	.016/0,41	.019/0,48			
G	.029/0,74	.040/1,02			
H	.028/0,71	.034/0,86			

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

[LittleDiode.com](http://LittleDiode.com)

Looking forward to providing you with the best possible service.